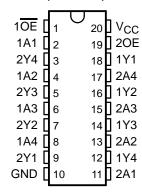
# SN54LVTH241, SN74LVTH241 3.3-V ABT OCTAL BUFFERS/DRIVERS WITH 3-STATE OUTPUTS

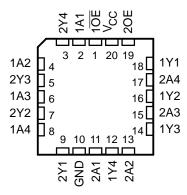
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- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- High-Impedance State During Power Up and Power Down
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V<sub>CC</sub>)
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V<sub>OLP</sub> (Output Ground Bounce)
   < 0.8 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C
- Power Off Disables Inputs/Outputs, Permitting Live Insertion
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs

#### SN54LVTH241 . . . J PACKAGE SN74LVTH241 . . . DB, DW, OR PW PACKAGE (TOP VIEW)



## SN54LVTH241 . . . FK PACKAGE (TOP VIEW)



#### description

These octal buffers/drivers are designed specifically for low-voltage (3.3-V)  $V_{CC}$  operation, with the capability to provide a TTL interface to a 5-V system environment.

The 'LVTH241 are organized as two 4-bit line drivers with separate output-enable ( $1\overline{OE}$ , 2OE) inputs. When  $1\overline{OE}$  is low or 2OE is high, the devices pass data from the A inputs to the Y outputs. When  $1\overline{OE}$  is high or 2OE is low, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When  $V_{CC}$  is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

The SN74LVTH241 is available in TI's shrink small-outline package (DB), which provides the same input/output (I/O) pin count and functionality of standard small-outline packages in less than half the printed circuit board area.

The SN54LVTH241 is characterized for operation over the full military temperature range of  $-55^{\circ}$ C to 125°C. The SN74LVTH241 is characterized for operation from  $-40^{\circ}$ C to  $85^{\circ}$ C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

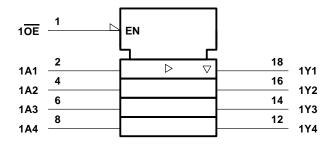


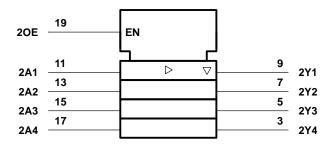
#### **FUNCTION TABLES**

INPU	JTS	OUTPUT				
1OE	1A	1Y				
L	Н	Н				
L	L	L				
Н	Χ	Z				

INP	JTS	OUTPUT
20E	2A	2Y
Н	Н	Н
Н	L	L
L	Χ	Z

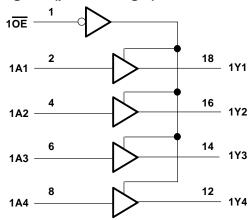
#### logic symbol†

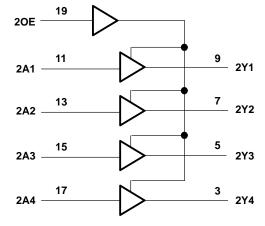




<sup>&</sup>lt;sup>†</sup>This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

### logic diagram (positive logic)





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#### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub>	0.5 V to 4.6 V
Input voltage range, V <sub>I</sub> (see Note 1)	
Voltage range applied to any output in the high state or power-off state, VO (see Note 1)	-0.5 V to 7 V
Current into any output in the low state, IO: SN54LVTH241	96 mA
SN74LVTH241	128 mA
Current into any output in the high state, IO (see Note 2): SN54LVTH241	48 mA
SN74LVTH241	64 mA
Input clamp current, $I_{IK}$ ( $V_I < 0$ )	50 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	50 mA
Maximum power dissipation at T <sub>A</sub> = 55°C (in still air) (see Note 3): DB package	0.6 W
DW package	1.6 W
PW package	0.7 W
Storage temperature range, T <sub>stg</sub> 6	5°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This current flows only when the output is in the high state and  $V_O > V_{CC}$ .

3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the *ABT Advanced BiCMOS Technology Data Book*.

#### recommended operating conditions (see Note 4)

					SN74LV	LINUT	
			MIN	MAX	MIN	MAX	UNIT
Vсс	Supply voltage		2.7	3.6	2.7	3.6	V
$V_{IH}$	High-level input voltage		2	FIN	2		V
VIL	Low-level input voltage					8.0	V
٧ <sub>I</sub>	Input voltage			5.5		5.5	V
ЮН	High-level output current		Ċ)	-24		-32	mA
loL	Low-level output current		700	48		64	mA
Δt/Δν	Input transition rise or fall rate	Outputs enabled	A.	10		10	ns/V
Δt/ΔV <sub>CC</sub>	Power-up ramp rate		200		200		μs/V
TA	Operating free-air temperature		-55	125	-40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

#### **SN54LVTH241, SN74LVTH241** 3.3-V ABT OCTAL BUFFERS/DRIVERS **WITH 3-STATE OUTPUTS**

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#### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS				54LVTH2	241	SN	LINUT				
	1	MIN	TYP <sup>†</sup>	MAX	MIN	TYP†	MAX	UNIT				
VIK	$V_{CC} = 2.7 \text{ V},$	I <sub>I</sub> = -18 mA			-1.2			-1.2	V			
	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	V <sub>CC</sub> -0	.2		V <sub>CC</sub> -0	.2						
	$V_{CC} = 2.7 \text{ V},$	2.4			2.4			$\Box$ $\lor$				
VOH	V <sub>CC</sub> = 3 V	$I_{OH} = -24 \text{ mA}$	2						V			
	ACC = 2 A	$I_{OH} = -32 \text{ mA}$				2						
	V <sub>CC</sub> = 2.7 V	I <sub>OL</sub> = 100 μA				0.2			0.2			
	ACC = 5.1 A	I <sub>OL</sub> = 24 mA				0.5			0.5			
\/-·		I <sub>OL</sub> = 16 mA				0.4			0.4	.,		
VOL	V 2.V	I <sub>OL</sub> = 32 mA				0.5			0.5	V		
	VCC = 3 V	I <sub>OL</sub> = 48 mA				0.55						
		I <sub>OL</sub> = 64 mA		Ũ	2			0.55				
	$V_{CC} = 0 \text{ or } 3.6 \text{ V},$	V <sub>I</sub> = 5.5 V			Q	10			10			
	V <sub>CC</sub> = 3.6 V	$V_I = V_{CC}$ or GND	Control inputs		Ç,	±1			±1	^		
łį		VI = VCC	Doto inputo		20	1			1	μΑ		
		V <sub>I</sub> = 0	Data inputs	4	70	-5			-5			
l <sub>off</sub>	$V_{CC} = 0$ ,	$V_{I}$ or $V_{O} = 0$ to 4.5	V			±100			±100	μΑ		
len en	V 2V	V <sub>I</sub> = 0.8 V	Doto inputo	75			75			^		
l(hold)	VCC = 3 V	V <sub>I</sub> = 2 V	Data inputs	<b>-</b> 75		<b>–</b> 75			μΑ			
lozh	V <sub>CC</sub> = 3.6 V,	VO = 3 V				5			5	μΑ		
lozL	V <sub>CC</sub> = 3.6 V,	V <sub>O</sub> = 0.5 V				-5			-5	μΑ		
I <sub>OZPU</sub> ‡	$V_{CC} = 0 \text{ to } 1.5 \text{ V},  $	$I_{O} = 0.5 \text{ V to 3 V}, \ \overline{OE}/C$	DE= don't care			±100			±100	μΑ		
I <sub>OZPD</sub> ‡	$V_{CC} = 1.5 \text{ V to } 0,  $	$V_{O} = 0.5 \text{ V to 3 V}, \overline{OE}/c$	OE= don't care			±100			±100	μΑ		
			Outputs high			0.19			0.19			
loo	$V_{CC} = 3.6 \text{ V},$	$I_{O} = 0$ ,	Outputs low	5				5	mA			
lcc	V <sub>I</sub> = V <sub>CC</sub> or GND	Outputs disabled			0.19			0.19	ША			
ΔI <sub>CC</sub> §	$V_{CC} = 3 \text{ V to } 3.6 \text{ V},$ Other inputs at $V_{CC}$	V to 3.6 V, One input at V <sub>CC</sub> – 0.6 V, outs at V <sub>CC</sub> or GND				0.2			0.2	mA		
Ci	V <sub>I</sub> = 3 V or 0	/ <sub>I</sub> = 3 V or 0						3		pF		
Co	V <sub>O</sub> = 3 V or 0				7			7		pF		

<sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ . ‡ This parameter is characterized but not tested.

<sup>§</sup> This is the increase in supply current for each input that is at the specified TTL voltage level rather than VCC or GND.

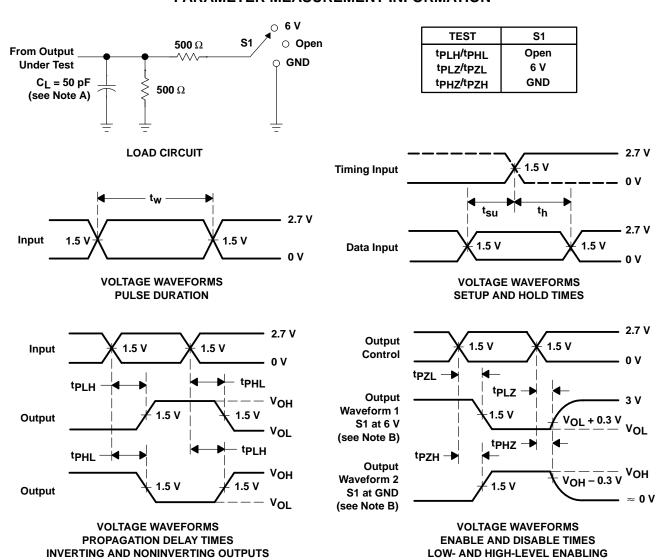
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# switching characteristics over recommended ranges of supply voltage and operating free-air temperature range, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 1)

		SN54LVTH241												
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 2.7 V		V <sub>CC</sub> = 3.3 V ± 0.3 V			V <sub>CC</sub> = 2.7 V		UNIT		
			MIN	MAX	MIN	MAX	MIN	TYP <sup>†</sup>	MAX	MIN	MAX			
t <sub>PLH</sub>	А	А	Λ	<b>&gt;</b>	1	3.7	Ü	1 4	1.1	2.3	3.5		3.9	ns
<sup>t</sup> PHL			•	1.2	3.5	ENL	3.7	1.3	2.2	3.4		3.6	115	
<sup>t</sup> PZH	OE or OE	>	1	4.6	6 Kr	5.5	1.1	2.7	4.5		5.4	ns		
t <sub>PZL</sub>		•	1.3	4.6		5.1	1.4	2.9	4.4		5	115		
<sup>t</sup> PHZ	OE or OE	<b>&gt;</b>	1.5	04.7		5.5	1.6	2.8	4.5		5.3	ns		
t <sub>PLZ</sub>	OL 01 OL	ſ	1.7	5		5.5	1.8	3	4.7		5.2	110		

 $<sup>\</sup>uparrow$  All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C.

#### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f \leq$  2.5 ns,  $t_f \leq$  2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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